



DRAM

256K x 4 DRAM

FAST PAGE MODE

AVAILABLE AS MILITARY SPECIFICATION

- SMD 5962-90617
- MIL-STD-883

FEATURES

- Industry standard pinout and timing
- All inputs, outputs and clocks are fully TTL compatible
- Single +5V±10% power supply
- Low power, 5mW standby; 175mW active, typical
- Optional FAST PAGE MODE access cycle
- Refresh modes: $\overline{\text{RAS}}$ -ONLY, $\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ and HIDDEN
- 512-cycle refresh distributed across 8ms
- Specifications guaranteed over full military temperature range (-55°C to +125°C)

OPTIONS

- Timing
 - 80ns access
 - 100ns access
 - 120ns access

MARKING

- Packages

Ceramic DIP (300 mil)	C	No. 103
Ceramic LCC	EC	No. 202

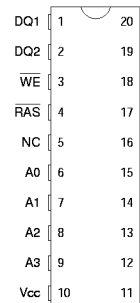
GENERAL DESCRIPTION

The MT4C4256 883C is a randomly accessed solid-state memory containing 1,048,576 bits organized in a 262,144 x4 configuration. During READ or WRITE cycles, each 4-bit word is uniquely addressed through the 18 address bits which are entered 9 bits (A0-A8) at a time. $\overline{\text{RAS}}$ is used to latch the first 9 bits and $\overline{\text{CAS}}$ the latter 9 bits. A READ or WRITE cycle is selected with the $\overline{\text{WE}}$ input. A logic HIGH on $\overline{\text{WE}}$ dictates READ mode while a logic LOW on $\overline{\text{WE}}$ dictates WRITE mode.

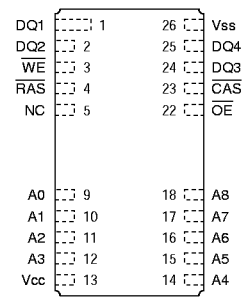
During a WRITE cycle, data in (D) is latched by the falling edge of $\overline{\text{WE}}$ or $\overline{\text{CAS}}$, whichever occurs last. If $\overline{\text{WE}}$ goes LOW prior to $\overline{\text{CAS}}$ going LOW, the output pins (Qs) remain open (High-Z) until the next $\overline{\text{CAS}}$ cycle. If $\overline{\text{WE}}$ goes LOW after data reaches the outputs (Qs), the outputs are activated and retain the selected cells' data as long as $\overline{\text{CAS}}$ remains LOW (regardless of $\overline{\text{WE}}$ or $\overline{\text{RAS}}$). This late $\overline{\text{WE}}$ pulse results in a READ-WRITE cycle. The four data inputs and four data

PIN ASSIGNMENT (Top View)

20-Pin DIP (D-8)



20-Pin LCC



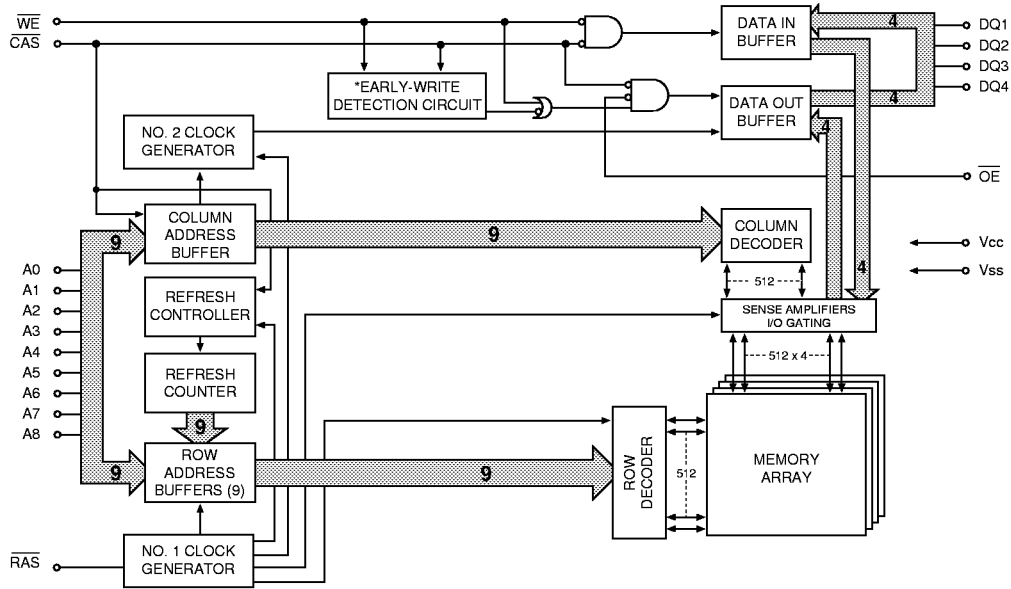
outputs are routed through four leads using common I/O, and information direction is controlled by $\overline{\text{WE}}$ and $\overline{\text{OE}}$.

FAST PAGE MODE operations allow faster data operations (READ, WRITE or READ-MODIFY-WRITE) within a row address (A0-A8) defined page boundary. The FAST PAGE MODE cycle is always initiated with a row address strobed-in by $\overline{\text{RAS}}$ followed by a column address strobed-in by $\overline{\text{CAS}}$. $\overline{\text{CAS}}$ may be toggled-in by holding $\overline{\text{RAS}}$ LOW and strobing-in different column addresses, thus executing faster memory cycles. Returning $\overline{\text{RAS}}$ HIGH terminates the FAST PAGE MODE operation.

Returning $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ HIGH terminates a memory cycle and decreases chip current to a reduced standby level. Also, the chip is preconditioned for the next cycle during the $\overline{\text{RAS}}$ high time. Memory cell data is retained in its correct state by maintaining power and executing any $\overline{\text{RAS}}$ cycle (READ, WRITE, $\overline{\text{RAS}}$ -ONLY, $\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$, or HIDDEN refresh) so that all 512 combinations of $\overline{\text{RAS}}$ addresses (A0-A8) are executed at least every 8ms, regardless of sequence.



FUNCTIONAL BLOCK DIAGRAM
FAST PAGE MODE



*NOTE: \overline{WE} LOW prior to \overline{CAS} LOW, EW detection circuit output is a HIGH (EARLY-WRITE)
 \overline{CAS} LOW prior to \overline{WE} LOW, EW detection circuit output is a LOW (LATE-WRITE)

TRUTH TABLE

FUNCTION		\overline{RAS}	\overline{CAS}	\overline{WE}	\overline{OE}	ADDRESSES		DATA IN/OUT
						'R	'C	DQ1-DQ4
Standby		H	H→X	X	X	X	X	High-Z
READ		L	L	H	L	ROW	COL	Data Out
EARLY-WRITE		L	L	L	X	ROW	COL	Data In
READ-WRITE		L	L	H→L	L→H	ROW	COL	Data Out, Data In
FAST-PAGE-MODE	1st Cycle	L	H→L	H	L	ROW	COL	Data Out
READ	2nd Cycle	L	H→L	H	L	n/a	COL	Data Out
FAST-PAGE-MODE	1st Cycle	L	H→L	L	X	ROW	COL	Data In
EARLY-WRITE	2nd Cycle	L	H→L	L	X	n/a	COL	Data In
FAST-PAGE-MODE	1st Cycle	L	H→L	H→L	L→H	ROW	COL	Data Out, Data In
READ-WRITE	2nd Cycle	L	H→L	H→L	L→H	n/a	COL	Data Out, Data In
RAS-ONLY REFRESH		L	H	X	X	ROW	n/a	High-Z
HIDDEN	READ	L→H→L	L	H	L	ROW	COL	Data Out
REFRESH	WRITE	L→H→L	L	L	X	ROW	COL	Data In
CAS-BEFORE-RAS REFRESH		H→L	L	X	X	X	X	High-Z



ABSOLUTE MAXIMUM RATINGS*

Voltage on Any Pin Relative to Vss -1.5V to +7.0V
 Storage Temperature Range -65°C to +150°C
 Power Dissipation 1W
 Lead Temperature (Soldering 5 Seconds) 270°C
 Junction Temperature (T_j) +175°C
 Short Circuit Output Current 50mA

*Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL PERFORMANCE CHARACTERISTICS

(Notes: 1, 6, 7) (-55°C ≤ T_C ≤ +125°C; V_{CC} = 5V ±10%)

PARAMETER/CONDITION	SYMBOL	MIN	MAX	UNITS	NOTES
Supply Voltage	V _{CC}	4.5	5.5	V	
Input High (Logic 1) Voltage, All Inputs	V _{IH}	2.4	V _{CC} +0.5	V	
Input Low (Logic 0) Voltage, All Inputs	V _{IL}	-0.5	0.8	V	
INPUT LEAKAGE CURRENT Any Input (0V ≤ V _{IN} ≤ 6.5V), All other pins not under test = 0V	I _I	-5	5	μA	
OUTPUT LEAKAGE CURRENT (Q is Disabled, 0V ≤ V _{OUT} ≤ 6.5V)	I _{OZ}	-5	5	μA	
OUTPUT LEVELS Output High Voltage (I _{OUT} = -5mA) Output Low Voltage (I _{OUT} = 4.2mA)	V _{OH} V _{OL}	2.4	0.4	V	

PARAMETER/CONDITION	SYMBOL	MAX			UNITS	NOTES
		-8	-10	-12		
STANDBY CURRENT: (TTL) (RAS = CAS = V _{IH})	I _{CC1}	3	3	3	mA	
STANDBY CURRENT: (CMOS) (RAS = CAS = V _{CC} - 0.2V; all other inputs = V _{CC} - 0.2V)	I _{CC2}	1	1	1	mA	
OPERATING CURRENT: Random READ/WRITE Average power supply current (RAS, CAS, Address Cycling: t _{RC} = t _{RC} (MIN))	I _{CC3}	70	60	50	mA	3, 4
OPERATING CURRENT: FAST PAGE MODE Average power supply current (RAS = V _{IL} , CAS, Address Cycling: t _{PC} = t _{PC} (MIN))	I _{CC4}	50	40	30	mA	3, 4
REFRESH CURRENT: RAS-ONLY Average power supply current (RAS Cycling, CAS = V _{IH} : t _{RC} = t _{RC} (MIN))	I _{CC5}	70	60	50	mA	3
REFRESH CURRENT: CAS-BEFORE-RAS Average power supply current (RAS, CAS, Address Cycling: t _{RC} = t _{RC} (MIN))	I _{CC6}	70	60	50	mA	3, 5



CAPACITANCE

PARAMETER	SYMBOL	MIN	MAX	UNITS	NOTES
Input Capacitance: (A0-A8), D	C _{I1}		7	pF	2
Input Capacitance: RAS, CAS, WE, OE	C _{I2}		7	pF	2
Input/Output Capacitance: (DQ1-DQ4)	C _O		8	pF	2

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Notes: 6, 7, 8, 9, 10, 11, 12, 13) (-55°C ≤ T_C ≤ +125°C; V_{CC} = 5V ± 10%)

AC CHARACTERISTICS	PARAMETER	SYM	-8		-10		-12		UNITS	NOTES
			MIN	MAX	MIN	MAX	MIN	MAX		
Random READ or WRITE cycle time	t _{RC}		150		180		210		ns	
READ-WRITE cycle time	t _{RWC}		195		235		275		ns	
FAST-PAGE-MODE READ or WRITE cycle time	t _{PC}		45		55		65		ns	
FAST-PAGE-MODE READ-WRITE cycle time	t _{PRWC}		90		110		130		ns	
Access time from RAS	t _{RAC}			80		100		120	ns	14
Access time from CAS	t _{CAC}			20		25		30	ns	15
Output Enable	t _{OE}			20		25		30	ns	23
Access time from column address	t _{AA}			40		50		60	ns	
Access time from CAS precharge	t _{CPA}			40		50		60	ns	
RAS pulse width	t _{RAS}	80	100,000	100	100,000	120	100,000		ns	
RAS pulse width (FAST PAGE MODE)	t _{RASP}	80	100,000	100	100,000	120	100,000		ns	
RAS hold time	t _{RSH}	20		25		30			ns	
RAS precharge time	t _{RP}	60		70		80			ns	
CAS pulse width	t _{CAS}	20	100,000	25	100,000	30	100,000		ns	
CAS hold time	t _{CSH}	80		100		120			ns	
CAS precharge time	t _{CPN}	10		12		15			ns	16
CAS precharge time (FAST PAGE MODE)	t _{CP}	10		12		15			ns	
RAS to CAS delay time	t _{RCD}	20	60	25	75	25	90		ns	17
CAS to RAS precharge time	t _{CRP}	5		5		10			ns	
Row address setup time	t _{ASR}	0		0		0			ns	
Row address hold time	t _{RAH}	10		15		15			ns	
RAS to column address delay time	t _{RAD}	15	40	20	50	20	60		ns	18
Column address setup time	t _{ASC}	0		0		0			ns	
Column address hold time	t _{CAH}	15		20		20			ns	
Column address hold time (referenced to RAS)	t _{AR}	60		70		80			ns	
Column address to RAS lead time	t _{RAL}	40		50		60			ns	
Read command setup time	t _{RCS}	0		0		0			ns	
Read command hold time (referenced to CAS)	t _{RCH}	0		0		0			ns	19
Read command hold time (referenced to RAS)	t _{RRH}	0		0		0			ns	19
CAS to output in Low-Z	t _{CLZ}	0		0		0			ns	



ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Notes: 6, 7, 8, 9, 10, 11, 12, 13) ($-55^{\circ}\text{C} \leq T_{\text{C}} \leq +125^{\circ}\text{C}$; $V_{\text{CC}} = 5\text{V} \pm 10\%$)

AC CHARACTERISTICS		-8		-10		-12			
PARAMETER	SYM	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
Output buffer turn-off delay	t_{OFF}	0	20	0	20	0	25	ns	20, 26
Output disable	t_{OD}		20		20		25	ns	26
$\overline{\text{WE}}$ command setup time	t_{WCS}	0		0		0		ns	21
Write command hold time	t_{WCH}	15		20		25		ns	
Write command hold time (referenced to $\overline{\text{RAS}}$)	t_{WCR}	60		70		80		ns	
Write command pulse width	t_{WP}	15		15		20		ns	
Write command to $\overline{\text{RAS}}$ lead time	t_{RWL}	20		25		30		ns	
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	20		25		30		ns	
Data-in setup time	t_{DS}	0		0		0		ns	22
Data-in hold time	t_{DH}	15		20		25		ns	22
Data-in hold time (referenced to $\overline{\text{RAS}}$)	t_{DHR}	60		70		80		ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ delay time	t_{RWD}	105		125		150		ns	21
Column address to $\overline{\text{WE}}$ delay time	t_{AWD}	65		75		90		ns	21
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ delay time	t_{CWD}	45		50		60		ns	21
Transition time (rise or fall)	t_{T}	3	50	3	50	3	50	ns	
Refresh period (512 cycles)	t_{REF}		8		8		8	ms	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ precharge time	t_{RPC}	0		0		0		ns	
$\overline{\text{CAS}}$ setup time ($\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ refresh)	t_{CSR}	10		10		10		ns	5
$\overline{\text{CAS}}$ hold time ($\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ refresh)	t_{CHR}	15		20		25		ns	5
$\overline{\text{OE}}$ hold time from $\overline{\text{WE}}$ during READ-MODIFY-WRITE cycle	t_{OEH}	20		20		25		ns	25
$\overline{\text{OE}}$ setup prior to $\overline{\text{RAS}}$ during HIDDEN REFRESH cycle	t_{ORD}	0		0		0		ns	24

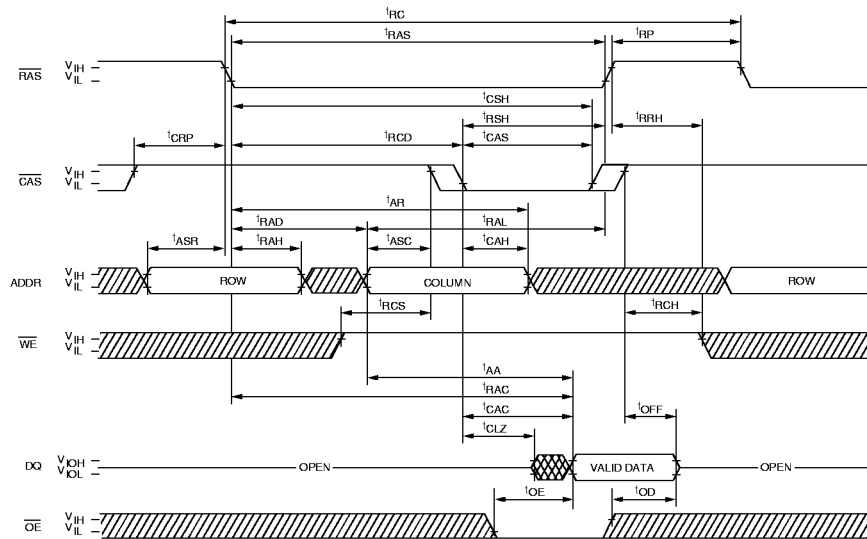


NOTES

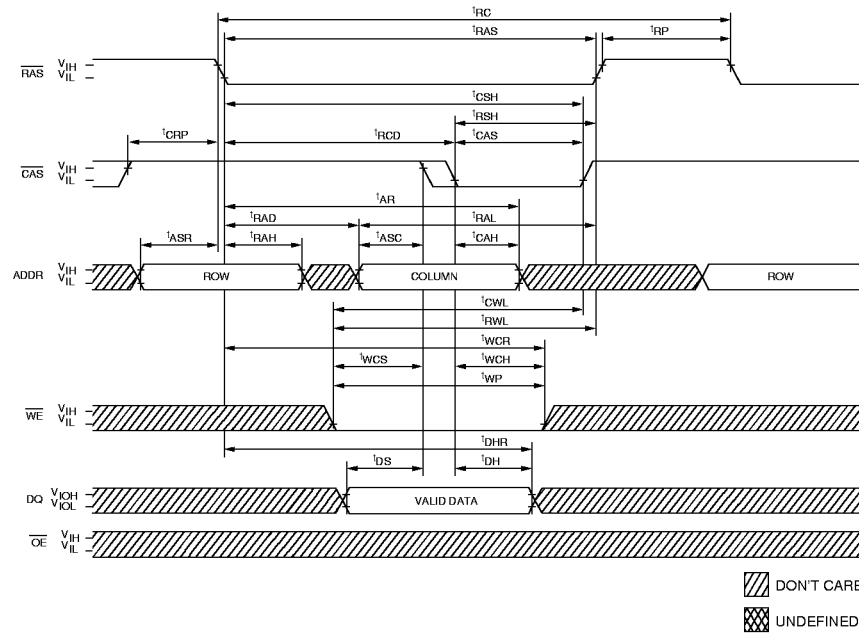
1. All voltages referenced to V_{SS} .
2. This parameter is sampled. $V_{CC} = 5V \pm 10\%$, $f = 1\text{ MHz}$.
3. I_{CC} is dependent on cycle rates.
4. I_{CC} is dependent on output loading and cycle rates. Specified values are obtained with minimum cycle time and the outputs open.
5. Enables on-chip refresh and address counters.
6. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range ($-55^{\circ}\text{C} \leq T_C \leq +125^{\circ}\text{C}$) is assured.
7. An initial pause of $100\mu\text{s}$ is required after power-up followed by any eight $\overline{\text{RAS}}$ cycles before proper device operation is assured. The eight $\overline{\text{RAS}}$ cycle wake-up should be repeated any time the $\overline{\text{REF}}$ refresh requirement is exceeded.
8. AC characteristics assume $t_T = 5\text{ ns}$. This parameter is not measured.
9. V_{IH} (MIN) and V_{IL} (MAX) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}).
10. In addition to meeting the transition rate specification, all input signals must transit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
11. If $\overline{\text{CAS}} = V_{IH}$, data outputs (DQs) are High-Z.
12. If $\overline{\text{CAS}} = V_{IL}$, data outputs (DQs) may contain data from the last valid READ cycle.
13. Measured with a load equivalent to 2 TTL gates and 100 pF .
14. Assumes that $t_{\text{RCD}} < t_{\text{RCD}}(\text{MAX})$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will increase by the amount that t_{RCD} exceeds the value shown.
15. Assumes that $t_{\text{RCD}} \geq t_{\text{RCD}}(\text{MAX})$.
16. If $\overline{\text{CAS}}$ is LOW at the falling edge of $\overline{\text{RAS}}$, DQs will be maintained from the previous cycle. To initiate a new cycle and clear the data out buffer, $\overline{\text{CAS}}$ must be pulsed HIGH for t_{CPN} .
17. Operation within the $t_{\text{RCD}}(\text{MAX})$ limit ensures that $t_{\text{RAC}}(\text{MAX})$ can be met. $t_{\text{RCD}}(\text{MAX})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{\text{RCD}}(\text{MAX})$ limit, then access time is controlled exclusively by t_{CAC} .
18. Operation within the $t_{\text{RAD}}(\text{MAX})$ limit ensures that $t_{\text{RAC}}(\text{MIN})$ and $t_{\text{CAC}}(\text{MIN})$ can be met. t_{RAD} (MAX) is specified as a reference point only; if t_{RAD} is greater than the specified $t_{\text{RAD}}(\text{MAX})$ limit, then access time is controlled exclusively by t_{AA} .
19. Either $\overline{\text{RCH}}$ or $\overline{\text{RRH}}$ must be satisfied for a READ cycle.
20. $t_{\text{OFF}}(\text{MAX})$ defines the time at which the output achieves the open circuit condition, and is not referenced to V_{OH} or V_{OL} .
21. t_{WCS} , t_{RWD} , t_{AWD} and t_{CWD} are not restrictive operating parameters. t_{WCS} applies to EARLY-WRITE cycles. t_{RWD} , t_{AWD} and t_{CWD} apply to READ-MODIFY-WRITE cycles. If $t_{\text{WCS}} \geq t_{\text{WCS}}(\text{MIN})$, the cycle is an EARLY-WRITE cycle and the data output will remain an open circuit throughout the entire cycle. If $t_{\text{RWD}} \geq t_{\text{RWD}}(\text{MIN})$, $t_{\text{AWD}} \geq t_{\text{AWD}}(\text{MIN})$ and $t_{\text{CWD}} \geq t_{\text{CWD}}(\text{MIN})$, the cycle is a READ-MODIFY-WRITE and the data output will contain data read from the selected cell. If neither of the above conditions is met, the state of data out is indeterminate. $\overline{\text{OE}}$ held HIGH and $\overline{\text{WE}}$ taken LOW after $\overline{\text{CAS}}$ goes LOW results in a LATE-WRITE ($\overline{\text{OE}}$ controlled) cycle. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are not applicable in a LATE-WRITE cycle.
22. These parameters are referenced to $\overline{\text{CAS}}$ leading edge in EARLY-WRITE cycles and $\overline{\text{WE}}$ leading edge in LATE-WRITE or READ-MODIFY-WRITE cycles.
23. If $\overline{\text{OE}}$ is tied permanently LOW, LATE-WRITE or READ-MODIFY-WRITE operations are not possible.
24. A HIDDEN REFRESH may also be performed after a WRITE cycle. In this case, $\overline{\text{WE}} = \text{LOW}$ and $\overline{\text{OE}} = \text{HIGH}$.
25. LATE-WRITE and READ-MODIFY-WRITE cycles must have both t_{OD} and $t_{\text{OE}}(\text{H})$ met ($\overline{\text{OE}}$ HIGH during WRITE cycle) in order to ensure that the output buffers will be open during the WRITE cycle. The DQs will provide the previously read data if $\overline{\text{CAS}}$ remains LOW and $\overline{\text{OE}}$ is taken back LOW after $t_{\text{OE}}(\text{H})$ is met. If $\overline{\text{CAS}}$ goes HIGH prior to $\overline{\text{OE}}$ going back LOW, the DQs will remain open.
26. The DQs open during READ cycles once t_{OD} or t_{OFF} occur. If $\overline{\text{CAS}}$ goes HIGH first, $\overline{\text{OE}}$ becomes a "don't care." If $\overline{\text{OE}}$ goes HIGH and $\overline{\text{CAS}}$ stays LOW, $\overline{\text{OE}}$ is not a "don't care;" and the DQs will provide the previously read data if $\overline{\text{OE}}$ is taken back LOW (while $\overline{\text{CAS}}$ remains LOW).



READ CYCLE

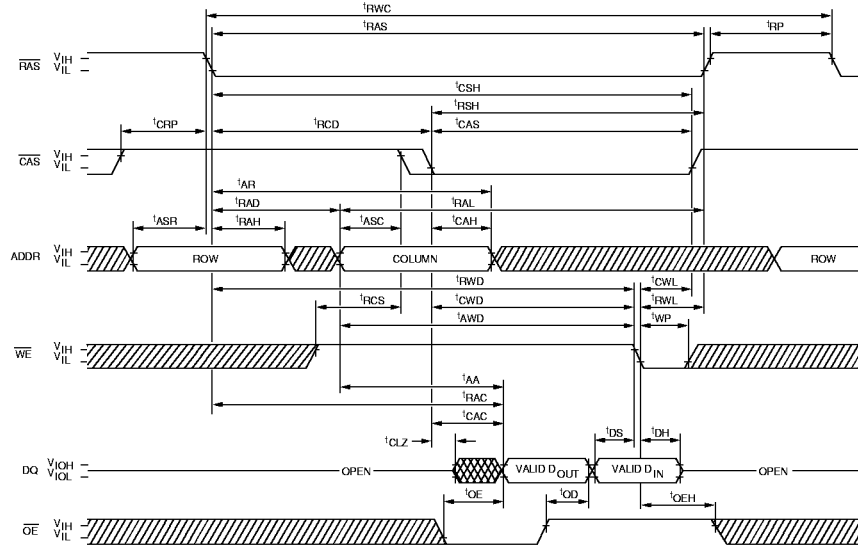


EARLY-WRITE CYCLE

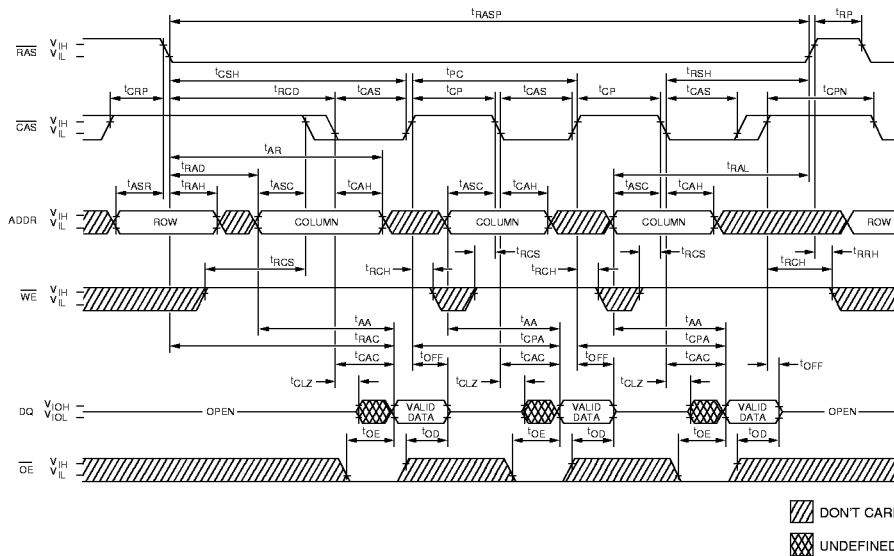




READ-WRITE CYCLE (LATE-WRITE and READ-MODIFY-WRITE CYCLES)



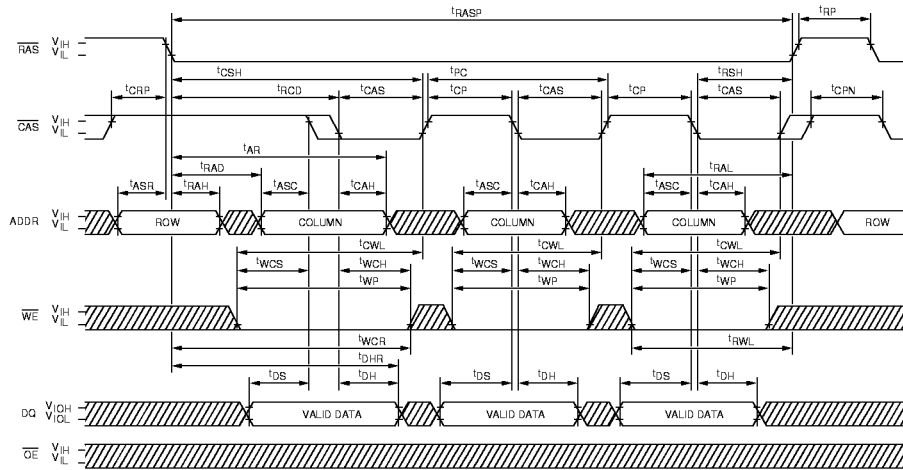
FAST-PAGE-MODE READ CYCLE



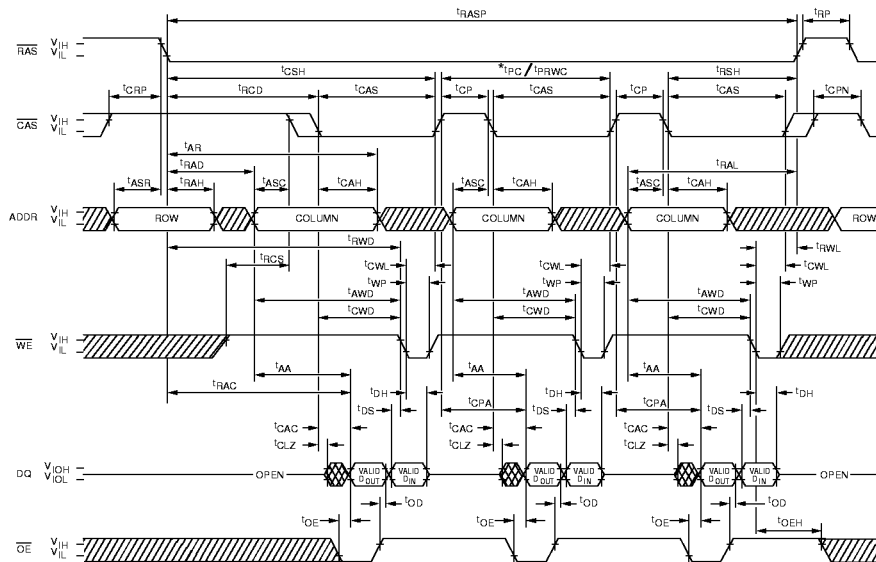
DONT CARE
 UNDEFINED



FAST-PAGE-MODE EARLY-WRITE CYCLE



FAST-PAGE-MODE READ-WRITE CYCLE
(LATE-WRITE and READ-MODIFY-WRITE CYCLES)

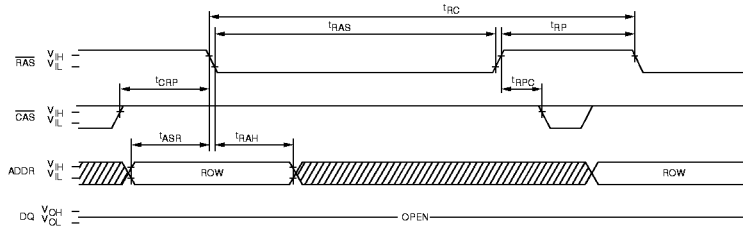


* t_{PC} = LATE-WRITE cycle
 t_{PRWC} = FAST READ-MODIFY-WRITE cycle

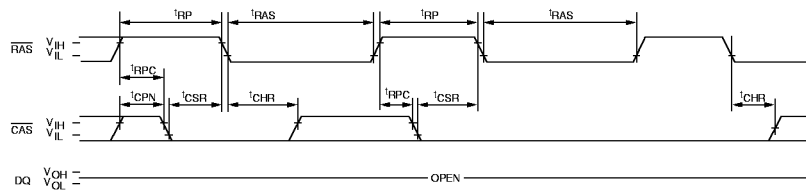
▨ DON'T CARE
▩ UNDEFINED



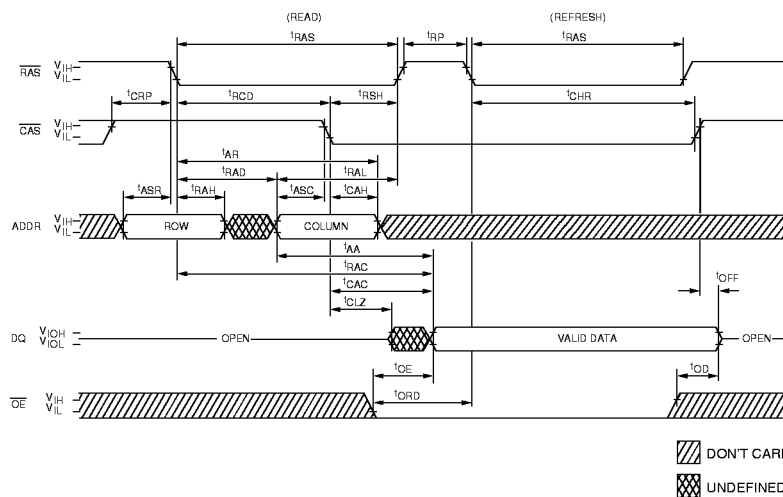
RAS-ONLY REFRESH CYCLE
(ADDR = A0-A8; WE = DON'T CARE)



CAS-BEFORE-RAS REFRESH CYCLE
(A0-A8, WE and OE = DON'T CARE)



HIDDEN REFRESH CYCLE²⁴
(WE = HIGH, OE = LOW)





ELECTRICAL TEST REQUIREMENTS

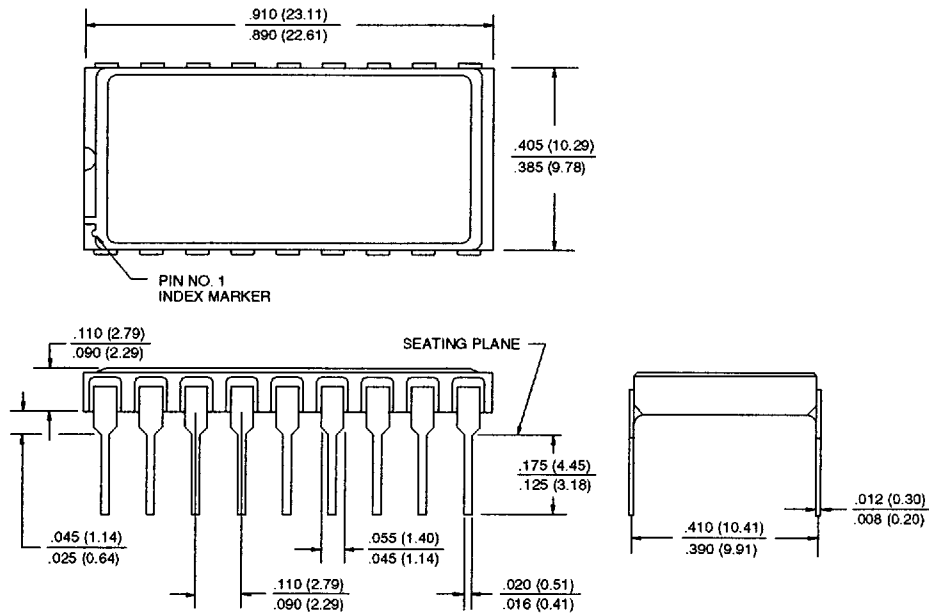
MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (per Method 5005, Table I)
INTERIM ELECTRICAL (PRE-BURN-IN) TEST PARAMETERS (Method 5004)	2, 8A, 10
FINAL ELECTRICAL TEST PARAMETERS (Method 5004)	1*, 2, 3, 7*, 8, 9, 10, 11
GROUP A TEST REQUIREMENTS (Method 5005)	1, 2, 3, 4**, 7, 8, 9, 10, 11
GROUP C AND D END-POINT ELECTRICAL PARAMETERS (Method 5005)	1, 2, 3, 7, 8, 9, 10, 11

* PDA applies to subgroups 1 and 7.

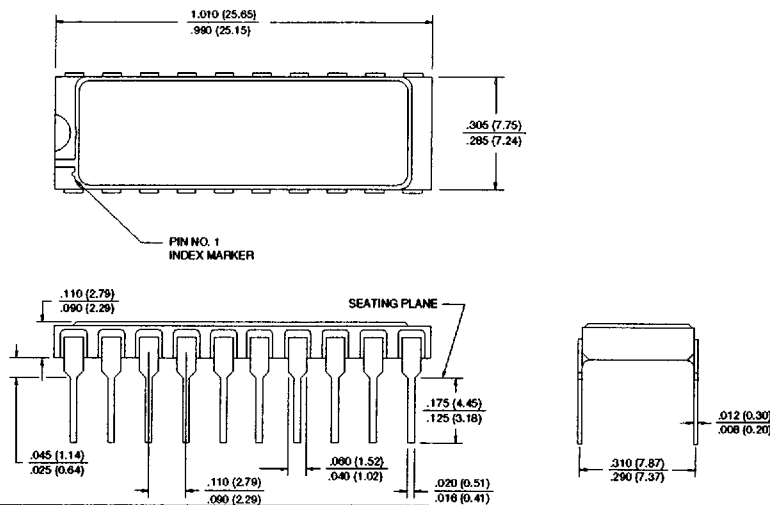
** Subgroup 4 shall be measured only for initial qualification and after process or design changes, which may affect input or output capacitance.



PACKAGE No. 102
18 CDIP (400 mils)

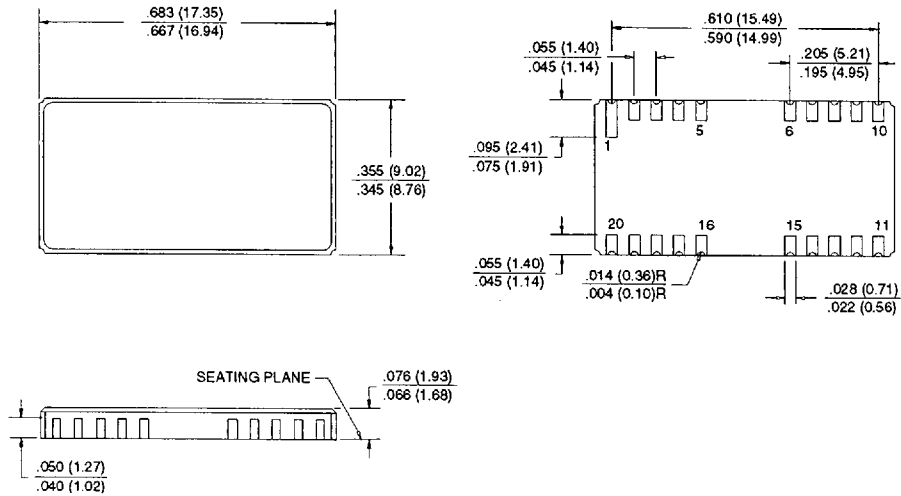


PACKAGE No. 103
20 CDIP D-8 (300 mils)





PACKAGE No. 202
20 CLCC



PACKAGE No. 203
28 CLCC

